EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	4542	(substrate or ("Al.sub.2 O.sub.3") or "SiC" or "AlN" or "GaN" or wafer or sapphire) with ((sacrificial or resist or photoresist or temporary) near4 (silicon or Si)) and ((silicon or Si) near8 (("111") or ("100") or ("110")))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/04 11:19
S2	24	(substrate or ("Al.sub.2 O.sub.3") or "SiC" or "AlN" or "GaN" or wafer or sapphire) with ((sacrificial or resist or photoresist or temporary) near4 (silicon or Si)) and ((silicon or Si) near8 (("111") or ("100") or ("110"))) and (sacrificial or resist or photoresist or temporary) with (nucleation or "AlN")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/04 11:16
S3	6	S1 and 438/619.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/04 11:15
S4	13	(substrate or ("Al.sub.2 O.sub.3") or "SiC" or "AlN" or "GaN" or wafer or sapphire) with ((sacrificial or resist or photoresist or temporary) near4 (silicon or Si)) and ((silicon or Si) near8 (("111") or ("100") or ("110"))) and (sacrificial or resist or photoresist or temporary) with "AlN"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/04 11:17
S5	4	(substrate or ("Al.sub.2 O.sub.3") or "SiC" or "AlN" or "GaN" or wafer or sapphire) with ((sacrificial or resist or photoresist or temporary) near4 (silicon or Si)) and ((silicon or Si) near8 (("111") or ("100") or ("110"))) and HVPE	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/18 14:09
S6	536	(substrate or ("Al.sub.2 O.sub.3") or "SiC" or "AlN" or "GaN" or wafer or sapphire) with ((sacrificial or resist or photoresist or temporary) near4 (silicon or Si)) and ((silicon or Si) near8 (("111") or ("100") or ("110"))) and (vapor$6 with (sacrificial or resist or photoresist or temporary))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/04 11:28

S7	710	(substrate or ("Al.sub.2 O.sub.3") or "SiC" or "AlN" or "GaN" or wafer or sapphire) with ((sacrificial or resist or photoresist or temporary) near4 (silicon or Si)) and ((silicon or Si) near8 (("111") or ("100") or ("110"))) and ((vapor$6 or evaporat$3) with (sacrificial or resist or photoresist or temporary))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/04 11:36
S8	260	(substrate or ("Al.sub.2 O.sub.3") or "SiC" or "AlN" or "GaN" or wafer or sapphire) with ((sacrificial or resist or photoresist or temporary) near4 (silicon or Si)) and ((silicon or Si) near8 (("111") or ("100") or ("110"))) and ((vaporiz$4 or evaporat$3) with (sacrificial or resist or photoresist or temporary))	•US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/04 11:48
S9	14	"1246233"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/04 12:07
S10	2	"6924159".pn.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/04 12:07
S11	3	("4792467" | "6583690").PN. OR ("6924159").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2007/05/04 12:09
S12	1	"6583690".pn.	US-PGPUB; USPAT; USOCR	OR	ON	2007/05/04 12:10
S13	4	2000-228539	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/04 12:15

S14	10	((vaporiz$4 or evaporat$) with sacrificial) and (free near2 standing) near3 (substrate or wafer)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/04 12:44
S15	19	(gap with sacrificial) and (free near2 standing) near3 (substrate or wafer)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/04 13:13
S16	1	10/573463	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/04 13:16
S17	2	(("6325850") or ("6802902")).PN.	US-PGPUB; USPAT	OR	OFF	2007/05/04 13:17
S18	1	10/516358	US-PGPUB; USPAT; IBM_TDB	OR	ON	2007/05/04 13:17
S19	1224	438/458.ccls. or 117/922.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/07 19:06
S20	283542	vaporization vaporiz$3 sublimation sublimat$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/07 19:06
S21	2740	heteroepitaxy heteroepitaxial	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/07 19:06

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S22	21499	"free-standing"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/07 19:06
S23	3	S19 and S20 and S21 and S22	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/07 19:07
S24	43	(vaporization or sublimation) and (438/458.ccls. or 117/922.ccls.)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/08 14:16

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1	((substrate or ("Al.sub.2 O.sub.3") or "SiC" or "AlN" or "GaN" or wafer or sapphire) with ((sacrificial or resist or photoresist or temporary) near4 (silicon or Si)) and ((silicon or Si) near8 (("111") or ("100") or ("110"))) and HVPE).clm.	US-PGPUB; USPAT	OR	ON	2007/05/18 14:10